

IN THE CLAIMS:

1. (currently amended) A crystalline material characterized in that it does not contain fluorides, with a composition in a roasted state corresponding to that of the material called ITQ-17 and in that it has a composition on an anhydrous base and in terms of moles of oxides upon being synthesized, unroasted, represented by: $xX_2O_3 \cdot (1-z)YO_2 \cdot zGeO_2 \cdot r/n R_nO$ wherein:

X is at least one trivalent element,

Y is one or more tetravalent elements other than germanium,

R is an organic structure directing compound,

x varies between 0 and 0.02, ~~preferably between 0 and 0.01,~~

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5,~~

r varies between 0.01 and 0.5, ~~preferably between 0.01 and 0.25,~~ and

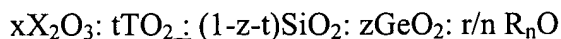
n is 1 or 2,

and whose most representative values of the X-ray diffraction angle are the following:

$2\theta \pm 0.5$ (degrees)	Intensity (I/I ₀)
6.89	w, m
9.57	vs
19.35	m
21.37	m
21.90	vs

vs: very strong, m: medium, w: weak.

2. (currently amended) A crystalline material according to claim 1, whose composition on an anhydrous base and in terms of moles of oxide upon being synthesized, unroasted, may be represented by:



wherein:

T is one or more tetravalent elements other than Ge or Si,

t varies between 0 and 0.15, ~~preferably between 0 and 0.10, and~~

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5, and "x", "X", "R", "r" and "n" have the meaning given in claim 1.~~

3. (previously presented) A crystalline material according to claim 1 or 2, wherein R is the cation 1-methyl-4-aza, 1-azoniumbicyclo [2.2.2] octane (DABMe⁺).

4. (previously presented) A crystalline material according to claim 1 or 2, wherein R is the cation 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene (d-DABBz)²⁺.

5. (currently amended) A crystalline material according to claim 1 wherein Y is one or more tetravalent elements selected ~~among~~ from the group consisting of Si, Sn, Ti and V and mixtures thereof.

6. (previously presented) A crystalline material according to claim 1 wherein Y is Si.

7. (currently amended) A crystalline material according to claim 1 or 2, wherein X is one or more trivalent ~~elements~~ element selected from the group consisting of B, Al, In, Ga, Fe and Cr.

8. (currently amended) A crystalline material according to claim 2, wherein T is one or more tetravalent elements selected ~~between~~ from the group consisting of V, Sn, and Ti and mixtures thereof.

9. (currently amended) A crystalline material according to claim 2, whose composition expressed in molar ratios is the following:

$\text{ROH}/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$ is between 0.5 and 0.01, ~~preferably between 0.25 and 0.01~~

$\text{GeO}_2/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$ is between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~

$(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)/\text{X}_2\text{O}_3$ is between ∞ and 50, ~~preferably between ∞ and 100~~ and

$\text{TO}_2/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$ is between 0.15 and 0, ~~preferably between 0.1 and 0.~~

10. (currently amended) A crystalline material according to claim 2, whose composition expressed in molar ratios is the following:

$\text{R}(\text{OH})_2/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$: between 0.25 and 0.005, ~~preferably between 0.125 and 0.005~~

$\text{GeO}_2/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~

$(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)/\text{X}_2\text{O}_3$: between ∞ and 50, ~~preferably between ∞ and 100~~

$\text{TO}_2/(\text{SiO}_2+\text{GeO}_2+\text{TO}_2)$: between 0.15 and 0, ~~preferably between 0.1 and 0.~~

11. (currently amended) A process for synthesizing a crystalline material that does not contain fluorides, with a composition in a roasted state corresponding to that of the material called ITQ-17 and in that it has a composition on an anhydrous base and in terms of moles of oxides upon being synthesized, unroasted, represented by:

$x\text{X}_2\text{O}_3$: $(1-z)\text{YO}_2$: $z\text{GeO}_2$: $r/n \text{R}_n\text{O}$

wherein:

X is at least one trivalent element,

Y is one or more tetravalent elements other than germanium,

R is an organic structure directing compound,

x varies between 0 and 0.02, ~~preferably between 0 and 0.01,~~

z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5,~~

r varies between 0.01 and 0.5, ~~preferably between 0.01 and 0.25,~~ and

n is 1 or 2,

and whose most representative values of the X-ray diffraction angle are the following:

2 θ +/- 0.5 (degrees)	Intensity (I/I ₀)
6.89	w, m
9.57	vs
19.35	m
21.37	m
21.90	vs

vs: very strong, m: medium, w: weak,

and whose process comprises:

- a) preparing a synthesis mixture that comprises at least:
 - a source of one or several tetravalent elements included under the name Y,
 - a source of Ge,
 - a source of at least one structure directing agent, and water;
- b) keeping the synthesis mixture at temperatures between 100 and 200° C, until the crystalline material is formed, and
- c) recovering the crystalline material.

12. (previously presented) A process according to claim 11, wherein the source of germanium and of the rest of the tetravalent elements is an oxide.

13. (currently amended) A process according to claim 11, wherein the synthesis mixture also comprises a source selected ~~among~~ from the group consisting of :

- a source of one or more trivalent elements, X,
- a source of one or more tetravalent elements other than Si and Ge, and
- ~~a mixture of both~~ mixtures thereof.

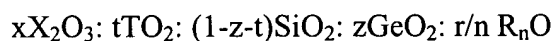
14. (currently amended) A process according to claim 11, wherein the source of the structure directing agent, R, is 1-methyl-4-aza, 1-azoniumbicyclo [2,2,2] octane hydroxide (DABMeOH), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(YO_2+GeO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1,~~
 $OH/(YO_2+GeO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03,~~
 $R/(YO_2+GeO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03,~~
 $GeO_2/(YO_2+GeO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04,~~ and
 $(YO_2+GeO_2)/X_2O_3$: between ∞ and 50, ~~preferably between ∞ and 100.~~

15. (currently amended) A process according to claim 11, wherein the source of the structure directing agent, R, is 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene hydroxide (d-DABBz(OH)₂), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(YO_2+GeO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1,~~ OH^{sup.-}
 YO_2+GeO_2 : between 3 and 0.01, ~~preferably between 1 and 0.03,~~ $R/(YO_2+GeO_2)$:
between 1.5 and 0.005, ~~preferably between 0.5 and 0.015,~~ GeO_2/YO_2+GeO_2 : between
0.657 and 0.02, ~~preferably between 0.5 and 0.04,~~ $(YO_2+GeO_2)/X_2O_3$: between ∞ and
50, ~~preferably between ∞ and 100.~~

16. (currently amended) A process according to claim 11, for preparing a material whose composition may be represented by the formula:



wherein:

T is one or more tetravalent elements other than Ge or Si,
t varies between 0 and 0.15, preferably between 0 and 0.10,
z is comprised between 0.02 and 0.67, ~~preferably between 0.04 and 0.5, and "x", "X",
"R", "r" and "n" have the meaning given in claim 1,~~ that comprises:

a) preparing a synthesis mixture that comprises at least: a source of silicon, a source of Ge, and a source of at least one structure directing agent (R) and water

- b) keeping the synthesis mixture at temperatures between 100 and 200° C, until the crystalline material is formed, and
- c) recovering the crystalline material.

17. (currently amended) A process according to claim 16, wherein the source of the structure directing agent (R) is 1-methyl-4-aza, 1-azoniumbicyclo [2,2,2] octane hydroxide (DABMeOH), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(SiO_2+GeO_2+TO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1~~, $OH^-/(SiO_2+GeO_2+TO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03~~, $R/(SiO_2+GeO_2+TO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03~~, $GeO_2/(SiO_2+GeO_2+TO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~, $(SiO_2+GeO_2+TO_2)/X_2O_3$: between ∞ and 50, ~~preferably between ∞ and 100~~, and $TO_2/(SiO_2+GeO_2+TO_2)$: between 0.15 and 0, ~~preferably between 0.1 and 0~~.

18. (currently amended) A process according to claim 16, wherein the structure directing agent, R, is 1,4-bis[N-(4-aza, 1-azoniumbicyclo [2,2,2] octane) methyl]benzene hydroxide (d-DABBz(OH)₂), and wherein the synthesis mixture has a composition expressed in terms of molar ratios in the following intervals:

$H_2O/(SiO_2+GeO_2+TO_2)$: between 100 and 0.01, ~~preferably between 50 and 0.1~~ $OH^-/(SiO_2+GeO_2+TO_2)$: between 3 and 0.01, ~~preferably between 1 and 0.03~~ $R/(SiO_2+GeO_2+TO_2)$: between 1.5 and 0.005, ~~preferably between 0.5 and 0.015~~ $GeO_2/(SiO_2+GeO_2+TO_2)$: between 0.67 and 0.02, ~~preferably between 0.5 and 0.04~~ $(SiO_2+GeO_2+TO_2)/X_2O_3$: between ∞ and 50, ~~preferably between ∞ and 100~~, $TO_2/(SiO_2+GeO_2+TO_2)$: between 0.15 and 0, ~~preferably between 0.1 and 0~~.

19. (currently amended) A process according to claim 16, wherein the synthesis mixture comprises one or more tetravalent elements, T, selected ~~among~~ from the group consisting of V, Sn, and Ti, and mixtures thereof.

20. (previously presented) A process according to claim 16, wherein the source of germanium, silicon and the rest of the tetravalent elements is an oxide.

21. (previously presented) A process according to claim 16, wherein the synthesis mixture also comprises a source of one or more trivalent elements, X.

22. (currently amended) A process according to claim 11 or 16 that also comprises a step of post-synthesis treatment of the material, whereby the organic component is removed from the structure by means of a technique selected ~~among~~ from the group consisting of extraction, roasting and both.

23. (currently amended) A material obtained according to the process of claim 22, characterized in that its diffraction diagram has the following as the most important lines:

$2\theta \pm 0.5$ (degrees)	Intensity (I/I ₀)
6.89	w, m
9.59	vs
21.27	m
21.87	m
27.87	vs ₂

24. (new) A crystalline material according to claim 1 wherein x varies between 0 and 0.01.

25. (new) A crystalline material according to claim 1 wherein z is comprised between 0.04 and 0.5.

26. (new) A crystalline material according to claim 1 wherein r varies between 0.01 and 0.25.

27. (new) A crystalline material according to claim 1 wherein x varies between 0 and 0.01, z is comprised between 0.04 and 0.5, and r varies between 0.01 and 0.25.

28. (new) A crystalline material according to claim 2 wherein t varies between 0 and 0.10.
29. (new) A crystalline material according to claim 2 wherein z is comprised between 0.04 and 0.5.
30. (new) A crystalline material according to claim 2 wherein t varies between 0 and 0.10, and z is comprised between 0.04 and 0.5.
31. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein x varies between 0 and 0.01.
32. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein z is comprised between 0.04 and 0.5.
33. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 r varies between 0.01 and 0.25.
34. (new) A process for synthesizing a crystalline material that does not contain fluorides according to claim 11 wherein x varies between 0 and 0.01, z is comprised between 0.04 and 0.5, and r varies between 0.01 and 0.25.